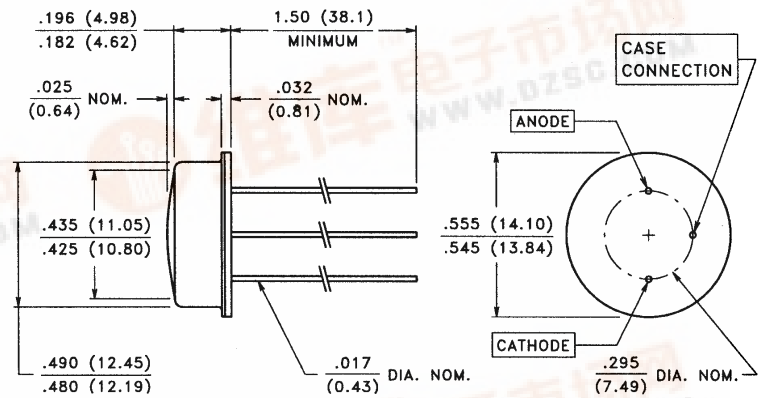


VTB Process Photodiodes

VTB6061J



PACKAGE DIMENSIONS inch (mm)



CASE 15 TO-8 HERMETIC
CHIP ACTIVE AREA: .058 in² (37.7 mm²)

PRODUCT DESCRIPTION

Large area planar silicon photodiode in a "flat" window, three lead TO-8 package. Chip is isolated from case. The third lead allows case to be grounded. These diodes have very high shunt resistance and have good blue response.

ABSOLUTE MAXIMUM RATINGS

Storage Temperature: -40°C to 110°C
Operating Temperature: -40°C to 110°C

ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also VTB curves, pages 21-22)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	VTB6061J			UNITS
			Min.	Typ.	Max.	
I _{SC}	Short Circuit Current	H = 100 fc, 2850 K	260	350		μA
TC I _{SC}	I _{SC} Temperature Coefficient	2850 K		.12	.23	%/°C
V _{OC}	Open Circuit Voltage	H = 100 fc, 2850 K		490		mV
TC V _{OC}	V _{OC} Temperature Coefficient	2850 K		-2.0		mV/°C
I _D	Dark Current	H = 0, V _R = 2.0 V			2.0	nA
R _{SH}	Shunt Resistance	H = 0, V = 10 mV		.10		GΩ
TC R _{SH}	R _{SH} Temperature Coefficient	H = 0, V = 10 mV		-8.0		%/°C
C _J	Junction Capacitance	H = 0, V = 0		8.0		nF
S _R	Sensitivity	365 nm		0.1		A/W
λ _{range}	Spectral Application Range		320		1100	nm
λ _p	Spectral Response - Peak			920		nm
V _{BR}	Breakdown Voltage		2	40		V
θ _{1/2}	Angular Resp. - 50% Resp. Pt.			±55		Degrees
NEP	Noise Equivalent Power			5.7 x 10 ⁻¹⁴ (Typ.)		W/√Hz
D*	Specific Detectivity			1.1 x 10 ¹³ (Typ.)		cm√Hz / W

